
Graphene and Emerging Materials for Post-CMOS Applications

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Published by

The Electrochemical Society

65 South Main Street, Building D
Pennington, NJ 08534-2839, USA

tel 609 737 1902

fax 609 737 2743

www.electrochem.org

ecstransactions™

Vol. 19 No. 5

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)
ISSN 1938-5862 (print)

ISBN 978-1-56677-713-1 (Hardcover)
ISBN 978-1-60768-063-5 (PDF)

Printed in the United States of America.

Table of Contents

Preface *iii*

Chapter 1 Plenary Session

Graphene: The Magic of Flat Carbon 3
K. S. Novoselov

Ge/III-V Channel Engineering for Future CMOS 9
S. Takagi, M. Sugiyama, T. Yasuda and M. Takenaka

Emerging Devices Based on Spin Transfer Torque Effect 21
R. Heindl and W. H. Rippard

Chapter 2 Graphene Physics

Development toward Wafer-Scale Graphene RF Electronics 35
*J. Moon, D. Curtis, M. Hu, D. Wong, P. Campbell, G. Jernigan, J. L. Tedesco,
B. VanMil, R. L. Myers-Ward, C. Eddy Jr., D. K. Gaskill, J. Robinson,
M. Fanton and P. Asbeck*

Synthesis, Characterization, and Properties of Large-Area Graphene Films 41
*X. Li, W. Cai, I. Jung, J. An, D. Yang, A. Velamakanni, R. Piner, L. Colombo
and R. S. Ruoff*

Freestanding Graphene and Its Applications 53
A. Banerjee and H. Grebel

Chapter 3 Characterization of Graphene

Optical and Conductivity Properties of Films from Liquid-Phase Exfoliation of
Natural Graphite 69
J. Obrzut and K. B. Migler

Surface Microscopy Characterizations of Large Size Graphene Films Grown by Surface Segregation on Ni and Transferred to Si/SiO₂ Substrate 75
D. Pandey, G. Prakash, Q. Yu, H. Cao, L. Jauregui, S. Pei and Y. P. Chen

HRTEM Observation of Mechanically Exfoliated Graphene from Natural Graphite and HOPG 81
S. Park, Y. Suh, H. Floresca and M. Kim

Effect of Surface Adsorbates on Graphene Probed by Hall-Effect and Raman Spectroscopy 87
B. Clafin, J. Park, K. Eyink, D. Tomich and J. Albrecht

Chapter 4 Epitaxial Graphene Electronics

Epitaxial Graphene: Designing a New Electronics Material 95
W. A. de Heer, C. Berger, X. S. Wu, M. Sprinkle, Y. Hu, M. Ruan, E. Conrad, M. Orlita and M. Potemski

Large-Area Epitaxial Graphene: Effect of Strain and Thickness on Electronic Properties 107
J. Robinson, M. Fanton, T. Stitt, T. Stitt, D. Snyder, E. Frantz, J. L. Tedesco, B. VanMil, G. Jernigan, P. Campbell, R. L. Myers-Ward, C. Eddy Jr. and D. K. Gaskill

Large-grained and Highly-ordered Graphene Synthesized by Radio Frequency Plasma-enhanced Chemical Vapor Deposition 111
Y. Woo, D. Kim, D. Jeon, H. Chung, S. Shin, X. Li, Y. Kwon, D. Seo, J. Shin, U. Chung and S. Seo

Chapter 5 Epitaxial Graphene on SiC

Epitaxial Graphene Growth on SiC Wafers 117
D. K. Gaskill, G. Jernigan, P. Campbell, J. L. Tedesco, J. Culbertson, B. VanMil, R. L. Myers-Ward, C. Eddy Jr., J. Moon, D. Curtis, M. Hu, D. Wong, C. McGuire, J. Robinson, M. Fanton, P. Stitt, T. Stitt, D. Snyder, X. Wang and E. Frantz

Surface Passivation Using Silane for Epitaxial Growth of Graphene on SiC substrate 125
B. Kang, S. Lim and B. Cho

3C-SiC Films Grown on Si(111) Substrates as a Template for Graphene Epitaxy	131
<i>M. Fanton, J. Robinson, B. Weiland and J. Moon</i>	

Improvement of Morphology and Free Carrier Mobility through Argon-Assisted Growth of Epitaxial Graphene on Silicon Carbide	137
<i>J. L. Tedesco, B. VanMil, R. L. Myers-Ward, J. Culbertson, G. Jernigan, P. Campbell, J. M. McCrate, S. A. Kitt, C. Eddy Jr. and D. K. Gaskill</i>	

Chapter 6

Carbon Nanostructures

Carbon Nanomaterials Standards Efforts at NIST	153
<i>J. A. Fagan</i>	

A Critical Assessment of the Synthesis of Diameter and Chirality Controlled CNTs in Zeolites	161
<i>J. Van Noyen, M. Roeffaers, G. De Cremer, T. Vosch, J. Hofkens, F. Clemente, P. Jacobs and B. Sels</i>	

Low Temperature Graphene Growth	175
<i>S. Kumar, N. McEvoy, T. Lutz, G. Keeley, N. Whiteside, W. Blau and G. S. Duesberg</i>	

Chapter 7

Graphene / High-k Stacks

Materials Science of Graphene for Novel Device Applications	185
<i>G. Lee, C. Gong, A. R. Pirkle, A. Venugopal, B. Lee, S. Park, L. Goux, M. Acik, R. Guzman, Y. J. Chabal, J. Kim, E. M. Vogel, R. M. Wallace, M. J. Kim, L. Colombo and K. Cho</i>	

Substrate-limited Mobility in Single- and Bi-layer Graphene on Dielectric Materials	201
<i>A. Klekachev, M. Cantoro, A. Nourbakhsh, M. H. van der Veen, F. Clemente, A. L. Stesmans, B. Sels, M. Heyns and S. De Gendt</i>	

Supramolecular Functionalization of Graphene	211
<i>W. Yang and H. Grennberg</i>	

In-situ Studies of High- κ Dielectrics for Graphene-Based Device	215
<i>A. R. Pirkle, Y. J. Chabal, L. Colombo and R. M. Wallace</i>	

Atomic-Layer-Deposited Al ₂ O ₃ as Gate Dielectrics for Graphene-Based Devices	225
<i>B. Lee, G. Mordi, T. Park, L. Goux, Y. J. Chabal, K. Cho, E. M. Vogel, M. Kim, L. Colombo, R. M. Wallace and J. Kim</i>	

Chapter 8 Graphene Composites and Gels

Novel Spectroscopic Platforms for Bio-Chemical Detection: Graphenated IR Screens	233
<i>A. Banerjee, K. Moeller and H. Grebel</i>	
Graphene Aerogels	241
<i>J. Wang and M. Ellsworth</i>	
Can Graphene be an Electrode Support for Pt in Formic Acid Electrooxidation?	249
<i>S. Murugesan, K. Myers and V. R. Subramanian</i>	
Graphene as a Permeable Ionic Barrier	259
<i>S. Sreevatsa, A. Banerjee and G. Haim</i>	

Chapter 9 Ge / III-V MOSFETS

CMOS Scaling Beyond 22 nm Node	267
<i>D. Sadana, S. W. Bedell, J. P. de Souza, Y. Sun, E. Kiewra, A. Reznicek, T. Adams, K. Fogel, G. G. Shahidi, C. Marchiori, D. J. Webb, M. Richter, C. Gerl, M. Sousa, J. Fompeyrine and R. Germann</i>	
Review of Current Status of III-V MOSFETS	275
<i>I. Thayne, R. Hill, M. Holland, X. Li, H. Zhou, D. Macintyre, S. Thoms, K. Kalna, C. Stanley, A. Asenov, R. Droopad and M. Paslack</i>	
Inter-band Tunnel Transistor Architecture using Narrow Gap Semiconductors	287
<i>S. Mookerjee, R. Krishnan, A. Vallett, T. Mayer and S. Datta</i>	

Chapter 10 III-V Process and Simulations

Integration of III-V and Si CMOS Devices by Molecular Beam Epitaxy	295
<i>D. Lubyshev, J. Fastenau and W. K. Liu</i>	

Controlled III/V Nanowire Growth by Selective-Area Vapour Phase Epitaxy 309
*M. Cantoro, G. Brammertz, O. Richard, H. Bender, F. Clemente, M. Leys,
S. Degroote, M. R. Caymax, M. Heyns and S. De Gendt*

Simulation of III-V HEMTs for High-speed Low-power Logic Applications 331
Y. Liu and M. Lundstrom

Chapter 11

III-V Devices

Monolithic III-V/Si Integration 345
*E. Fitzgerald, M. T. Bulsara, Y. Bai, C. Cheng, W. K. Liu, D. Lubyshev,
J. Fastenau, Y. Wu, M. Urtega, W. Ha, J. Bergman, B. Briar, C. Drazek,
N. Daval, F. Letertre, W. E. Hoke, J. R. LaRoche, K. J. Herrick and T. E. Kazior*

InGaAs MOSCAPs and Self-Aligned Inversion-channel MOSFETs with 351
Al₂O₃/Ga₂O₃(Gd₂O₃) as a Gate Dielectric
T. Lin, H. Chiu, P. Chang, W. Lee, T. Chiang, J. R. Kwo, W. Tsai and M. Hong

III-V/Ge Channel Engineering for Future CMOS 361
*M. Wistey, U. Singisetti, G. Burek, E. Kim, B. J. Thibeault, A. Nelson,
J. Cagnon, Y. Lee, S. R. Bank, S. Stemmer, P. C. McIntyre, A. C. Gossard and
M. J. Rodwell*

Chapter 12

III-V Interfaces

Electrical Properties of III-V/Oxide Interfaces 375
*G. Brammertz, H. Lin, K. Martens, A. Alian, C. Merckling, J. Penaud, D. Kohen,
W. Wang, S. Sioncke, A. Delabie, M. Meuris, M. R. Caymax and M. Heyns*

Surface Studies of III-V Materials: Oxidation Control and Device Implications 387
*C. Hinkle, M. Milojevic, A. Sonnet, H. Kim, J. Kim, E. M. Vogel and
R. M. Wallace*

Author Index 405